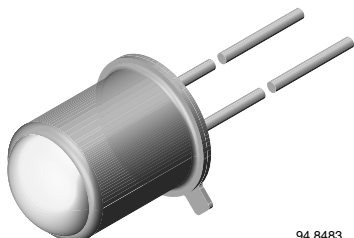


Infrared Emitting Diode, RoHS Compliant, 950 nm, GaAs



94 8483

FEATURES

- Package type: leaded
- Package form: TO-18
- Dimensions (in mm): \varnothing 4.7
- Peak wavelength: $\lambda_p = 950$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 5^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

DESCRIPTION

TSTS7100 is an infrared, 950 nm emitting diode in GaAs technology in a hermetically sealed TO-18 package with lens.

APPLICATIONS

- Radiation source in near infrared range

PRODUCT SUMMARY

| COMPONENT | I_e (mW/sr) | φ (deg) | λ_p (nm) | t_r (ns) |
|-----------|---------------|-----------------|------------------|------------|
| TSTS7100 | > 10 | ± 5 | 950 | 800 |

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

| ORDERING CODE | PACKAGING | REMARKS | PACKAGE FORM |
|---------------|-----------|------------------------------|--------------|
| TSTS7100 | Bulk | MOQ: 1000 pcs, 1000 pcs/bulk | TO-18 |

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
|-------------------------------------|---|------------|---------------|------------------|
| Reverse voltage | | V_R | 5 | V |
| Forward current | $T_{case} \leq 25^\circ\text{C}$ | I_F | 250 | mA |
| Peak forward current | $t_p/T = 0.5, t_p \leq 100 \mu\text{s}, T_{case} \leq 25^\circ\text{C}$ | I_{FM} | 500 | mA |
| Surge forward current | $t_p \leq 100 \mu\text{s}$ | I_{FSM} | 2.5 | A |
| Power dissipation | | P_V | 170 | mW |
| | $T_{case} \leq 25^\circ\text{C}$ | P_V | 500 | mW |
| Junction temperature | | T_j | 100 | $^\circ\text{C}$ |
| Storage temperature range | | T_{stg} | - 55 to + 100 | $^\circ\text{C}$ |
| Thermal resistance junction/ambient | leads not soldered | R_{thJA} | 450 | K/W |
| Thermal resistance junction/case | leads not soldered | R_{thJC} | 150 | K/W |

Note

$T_{amb} = 25^\circ\text{C}$, unless otherwise specified



Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

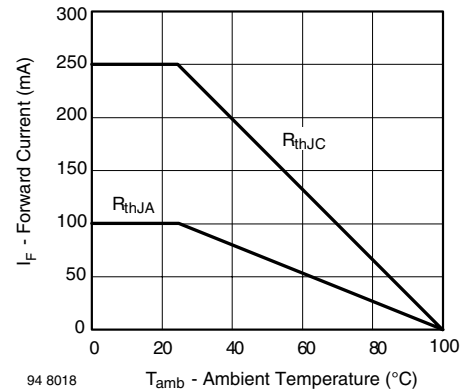


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS | | | | | | |
|-------------------------------------|---|-----------------|------|---------|------|-------|
| PARAMETER | TEST CONDITION | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| Forward voltage | $I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$ | V_F | | 1.3 | 1.7 | V |
| Temperature coefficient of V_F | $I_F = 100 \text{ mA}$ | TK_{V_F} | | - 1.3 | | mV/K |
| Breakdown voltage | $I_R = 100 \text{ } \mu\text{A}$ | $V_{(BR)}$ | 5 | | | V |
| Junction capacitance | $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, $E = 0$ | C_j | | 30 | | pF |
| Radiant intensity | $I_F = 100 \text{ mA}$, $t_p = 20 \text{ ms}$ | I_e | 10 | | 50 | mW/sr |
| Radiant power | $I_F = 100 \text{ mA}$, $t_p \leq 20 \text{ ms}$ | ϕ_e | | 7 | | mW |
| Temperature coefficient of ϕ_e | $I_F = 100 \text{ mA}$ | TK_{ϕ_e} | | - 0.8 | | %/K |
| Angle of half intensity | | φ | | ± 5 | | deg |
| Peak wavelength | $I_F = 100 \text{ mA}$ | λ_p | | 950 | | nm |
| Spectral bandwidth | $I_F = 100 \text{ mA}$ | $\Delta\lambda$ | | 50 | | nm |
| Rise time | $I_F = 100 \text{ mA}$ | t_r | | 800 | | ns |
| | $I_F = 1.5 \text{ A}$, $t_p/T = 0.01$, $t_p \leq 10 \text{ } \mu\text{s}$ | t_r | | 400 | | ns |
| Virtual source diameter | | d | | 1.5 | | mm |

Note
 $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified

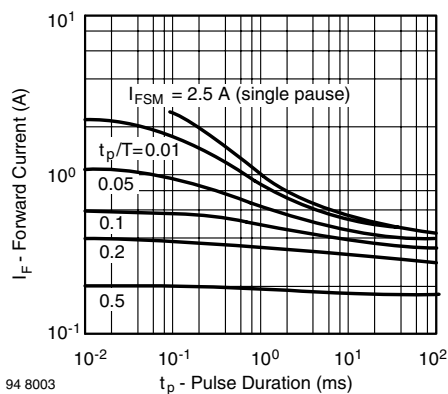
BASIC CHARACTERISTICS
 $T_{amb} = 25 \text{ }^\circ\text{C}$, unless otherwise specified


Fig. 3 - Pulse Forward Current vs. Pulse Duration

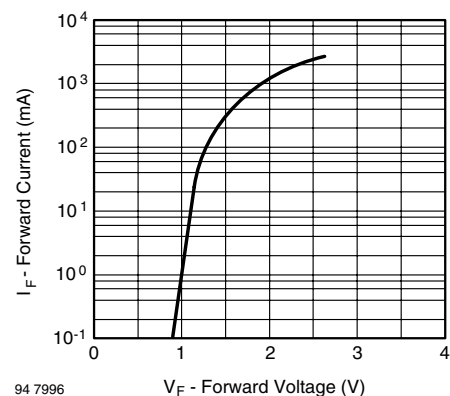


Fig. 4 - Forward Current vs. Forward Voltage



Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

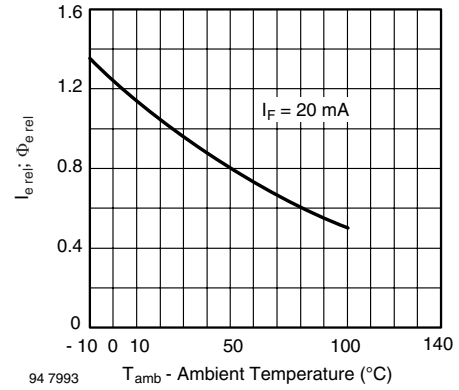


Fig. 8 - Rel. Radiant Intensity/Power vs. Ambient Temperature

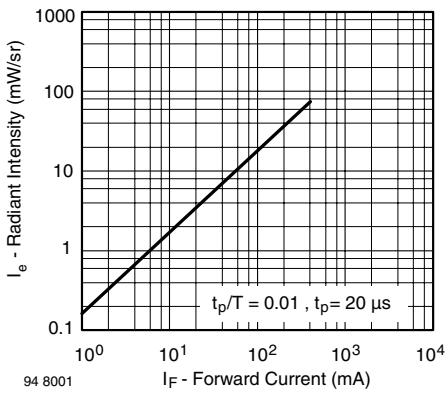


Fig. 6 - Radiant Intensity vs. Forward Current

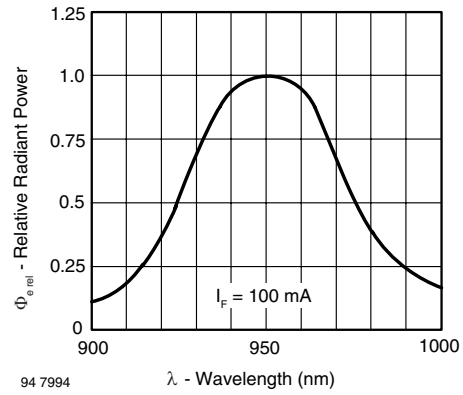


Fig. 9 - Relative Radiant Power vs. Wavelength

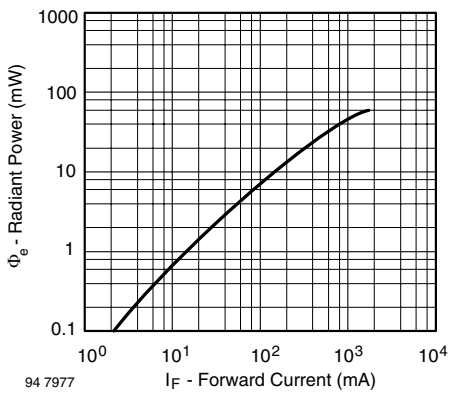


Fig. 7 - Radiant Power vs. Forward Current

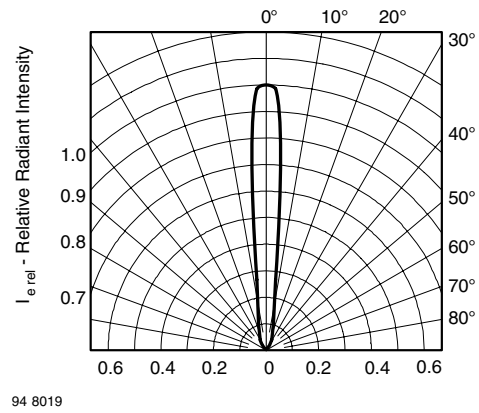
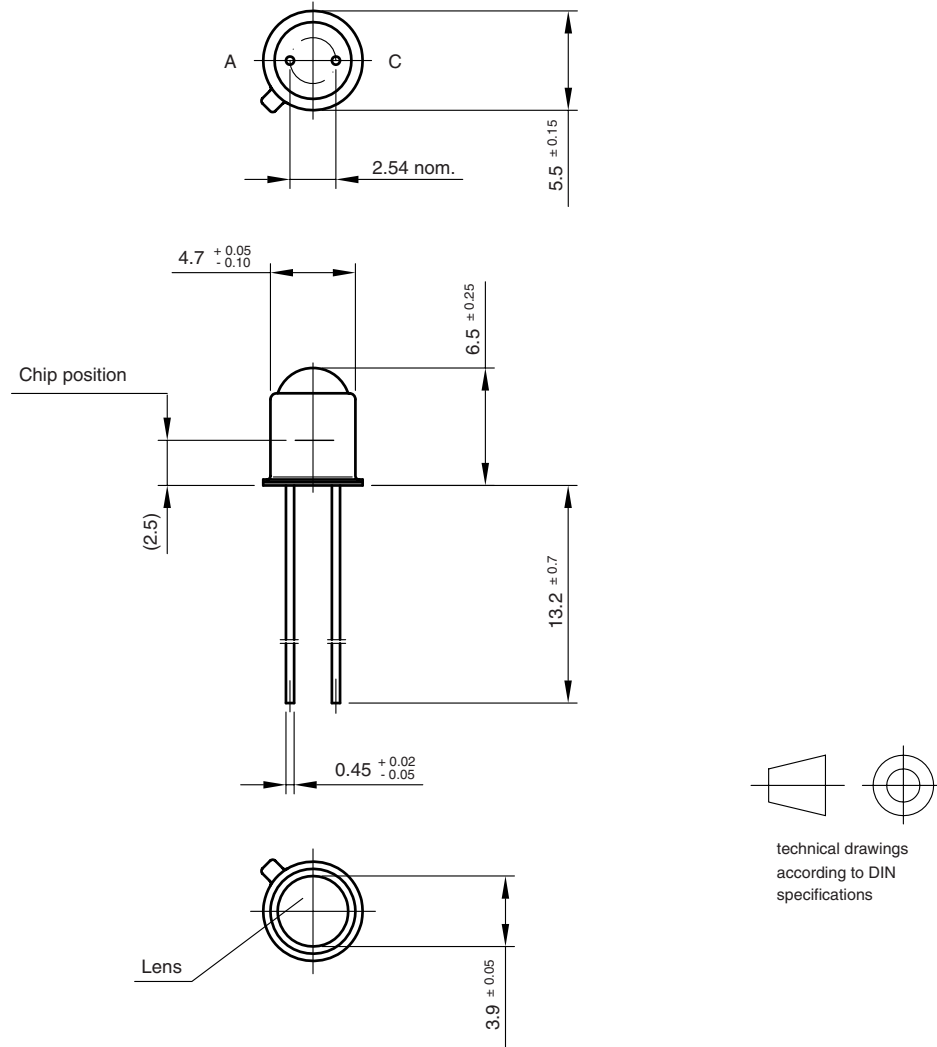


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement



PACKAGE DIMENSIONS in millimeters



Drawing-No.: 6.503-5002.02-4

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- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
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- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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